SWITCHMODE™ Series NPN Silicon Power Transistors

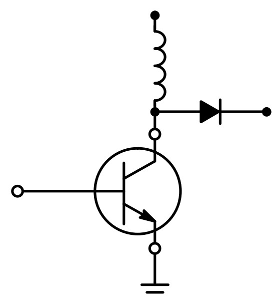
2N6547

The 2N6547 transistor is designed for high–voltage, high–speed, power switching in inductive circuits where fall time is critical. They are particularly suited for 115 and 220 volt line operated switch–mode applications such as:

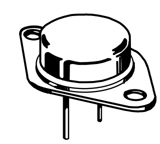
- Switching Regulators
- PWM Inverters and Motor Controls
- Solenoid and Relay Drivers
- Deflection Circuits

Specification Features

- High Temperature Performance Specified for:
  - Reversed Biased SOA with Inductive Loads
  - Switching Times with Inductive Loads
  - Saturation Voltages
  - Leakage Currents



15 AMPERE
NPN SILICON
POWER TRANSISTORS
300 and 400 VOLTS
175 WATTS



CASE 1–07
TO–204AA
(TO–3)

MAXIMUM RATINGS (1)

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	$V_{CEO(sus)}$	400	Vdc
Collector–Emitter Voltage	$V_{CEX(sus)}$	450	Vdc
Collector–Emitter Voltage	V_{CEV}	850	Vdc
Emitter Base Voltage	V_{EB}	9.0	Vdc
Collector Current — Continuous — Peak (2)	I_C I_{CM}	15 30	Adc
Base Current — Continuous — Peak (2)	I_B I_{BM}	10 20	Adc
Emitter Current — Continuous — Peak (2)	I_E I_{EM}	25 35	Adc
Total Power Dissipation @ T_C = 25°C @ T_C = 100°C Derate above 25°C	P_D	 175 100 1.0	Watts W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.0	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8″ from Case for 5 Seconds	T_L	275	°C

***ELECTRICAL CHARACTERISTICS** (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS (1)					
Collector–Emitter Sustaining Voltage (I_C = 100 mA, I_B = 0)	 2N6546 2N6547	$V_{CEO(sus)}$	 300 400	 — —	Vdc
Collector–Emitter Sustaining Voltage (I_C = 8.0 A, V_{clamp} = Rated V_{CEX}, T_C = 100°C) (I_C = 15 A, V_{clamp} = Rated V_{CEO} = 100 V, T_C = 100°C)	 2N6546 2N6547 2N6546 2N6547	$V_{CEX(sus)}$	 350 450 200 300	 — — — —	Vdc
Collector Cutoff Current (V_{CEV} = Rated Value, $V_{BE(off)}$ = 1.5 Vdc) (V_{CEV} = Rated Value, $V_{BE(off)}$ = 1.5 Vdc, T_C = 100°C)		I_{CEV}	 — —	 1.0 4.0	mAdc
Collector Cutoff Current (V_{CE} = Rated V_{CEV}, R_{BE} = 50 Ω, T_C = 100°C)		I_{CER}	—	5.0	mAdc
Emitter Cutoff Current (V_{EB} = 9.0 Vdc, I_C = 0)		I_{EBO}	—	1.0	mAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with base forward biased t = 1.0 s (non–repetitive) (V_{CE} = 100 Vdc)		$I_{S/b}$	0.2	—	Adc
ON CHARACTERISTICS (1)					
DC Current Gain (I_C = 5.0 Adc, V_{CE} = 2.0 Vdc) (I_C = 10 Adc, V_{CE} = 2.0 Vdc)		h_{FE}	 1 2 6.0	 60 30	—
Collector–Emitter Saturation Voltage (I_C = 10 Adc, I_B = 2.0 Adc) (I_C = 15 Adc, I_B = 3.0 Adc) (I_C = 10 Adc, I_B = 2.0 Adc, T_C = 100°C)		$V_{CE(sat)}$	 — — —	 1.5 5.0 2.5	Vdc
Base–Emitter Saturation Voltage (I_C = 10 Adc, I_B = 2.0 Adc) (I_C = 10 Adc, I_B = 2.0 Adc, T_C = 100°C		$V_{BE(sat)}$	 — —	 1.6 1.6	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain — Bandwidth Product (I_C = 500 mAdc, V_{CE} = 10 Vdc, f_{test} = 1.0 MHz)		f_T	6.0	28	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f_{test} = 1.0 MHz)		C_{ob}	125	500	pF

SWITCHING CHARACTERISTICS

Resistive Load					
Delay Time	(V_{CC} = 250 V, I_C = 10 A, I_{B1} = I_{B2} = 2.0 A, t_p = 100 μs, Duty Cycle ≤ 2.0%)	t_d	—	0.05	μs
Rise Time		t_r	—	1.0	μs
Storage Time		t_s	—	4.0	μs
Fall Time		t_f	—	0.7	μs
Inductive Load, Clamped					
Storage Time	(I_C = 10 A(pk), V_{clamp} = Rated V_{CEX}, I_{B1} = 2.0 A, $V_{BE(off)}$ = 5.0 Vdc, T_C = 100°C)	t_s	—	5.0	μs
Fall Time		t_f	—	1.5	μs
			Typical		
Storage Time	(I_C = 10 A(pk), V_{clamp} = Rated V_{CEX}, I_{B1} = 2.0 A, $V_{BE(off)}$ = 5.0 Vdc, T_C = 25°C)	t_s	2.0		μs
Fall Time		t_f	0.09		μs

*Indicates JEDEC Registered Data.
(1) Pulse Test: Pulse Width = 300 μs, Duty Cycle = 2%.

TYPICAL ELECTRICAL CHARACTERISTICS

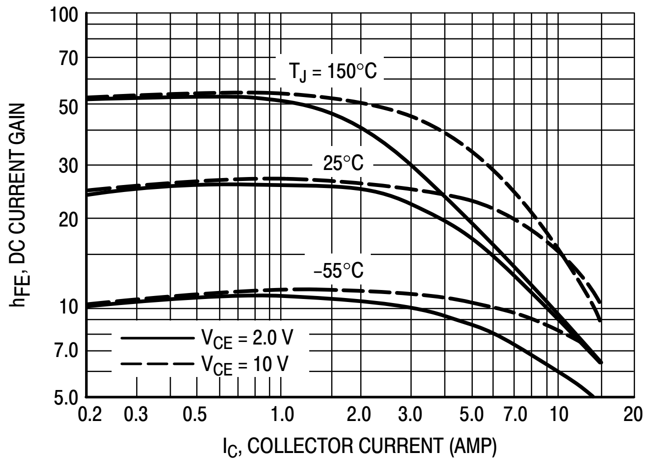


Figure 1. DC Current Gain

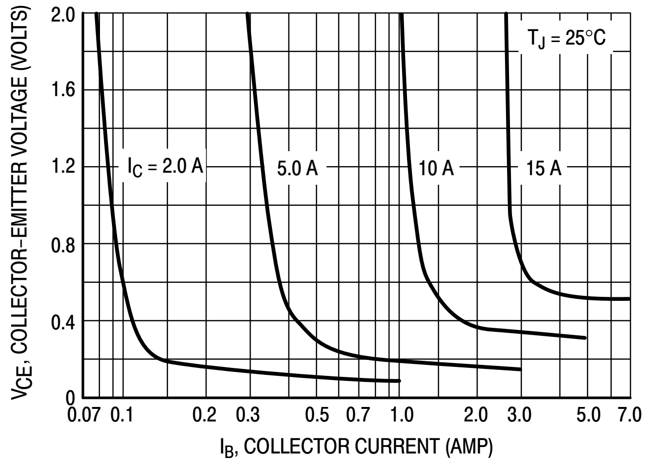


Figure 2. Collector Saturation Region

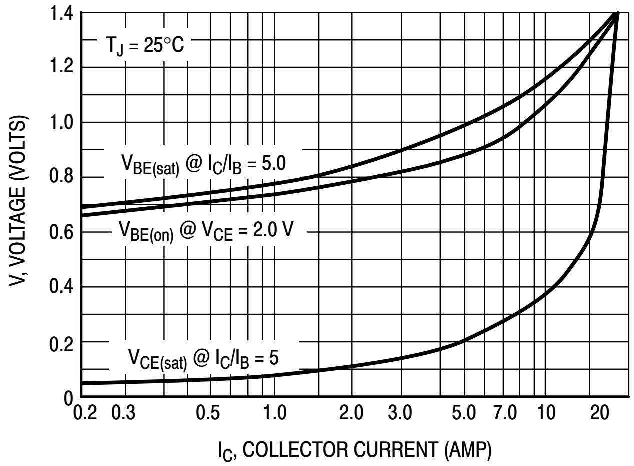


Figure 3. “On” Voltages

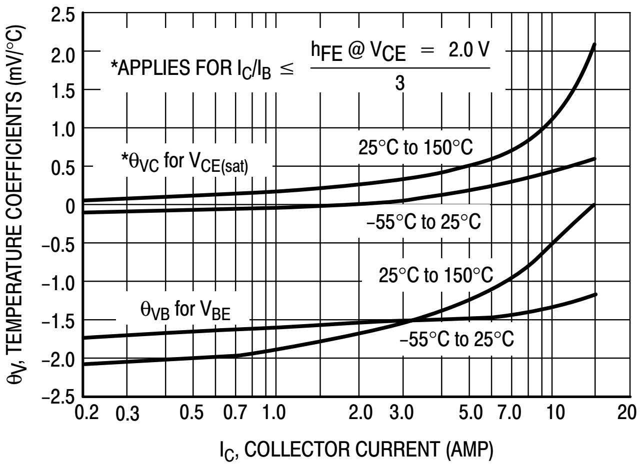


Figure 4. Temperature Coefficients

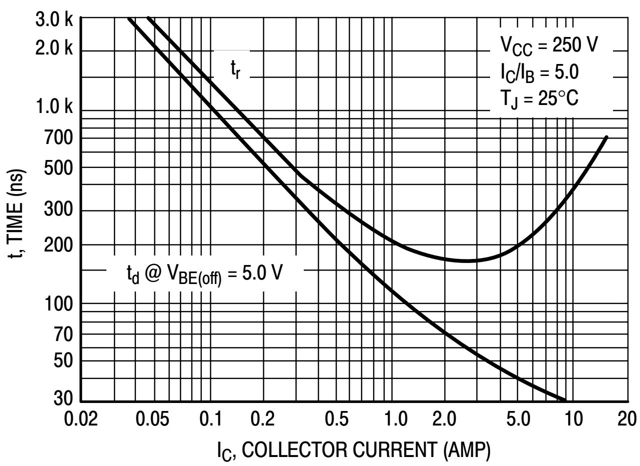


Figure 5. Turn−On Time

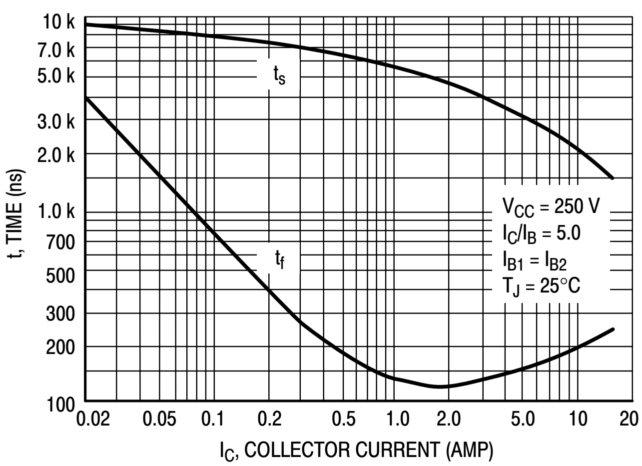


Figure 6. Turn−Off Time

MAXIMUM RATED SAFE OPERATING AREAS

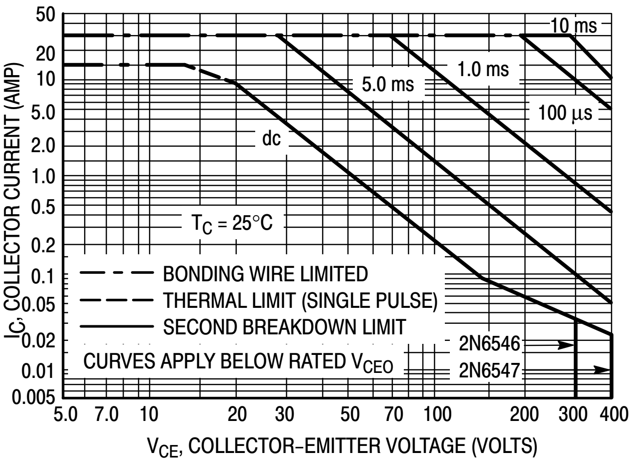


Figure 7. Forward Bias Safe Operating Area

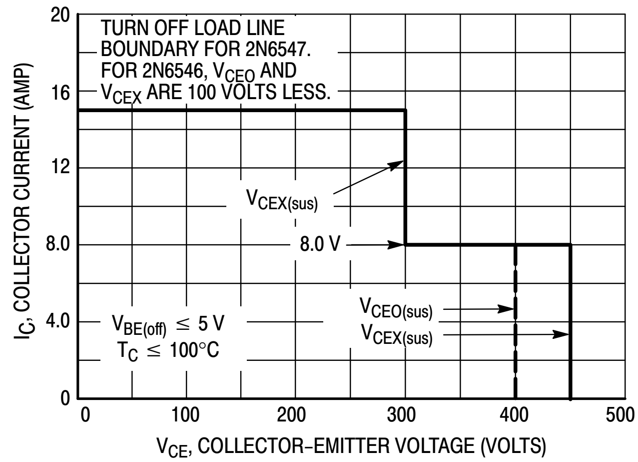


Figure 8. Reverse Bias Safe Operating Area

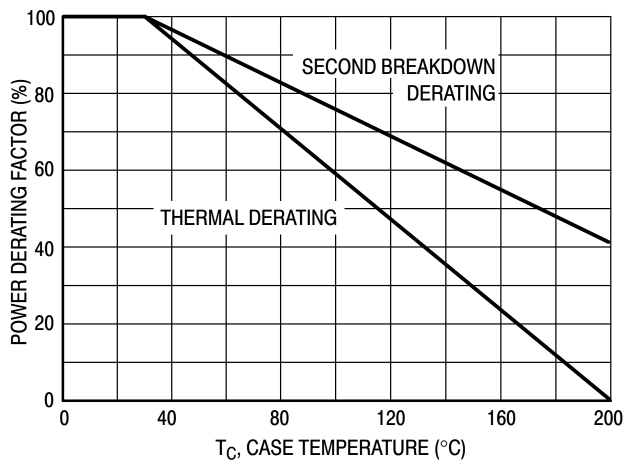


Figure 9. Power Derating

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 7 is based on $T_C = 25°C$; $T_{J(pk)}$ is variable depending on power level. Second breakdown pulse limits are valid for duty cycles to 10% but must be derated when $T_C \geq 25°C$. Second breakdown limitations do not derate the same as thermal limitations. Allowable current at the voltages shown on Figure 7 may be found at any case temperature by using the appropriate curve on Figure 9.

$T_{J(pk)}$ may be calculated from the data in Figure 10. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

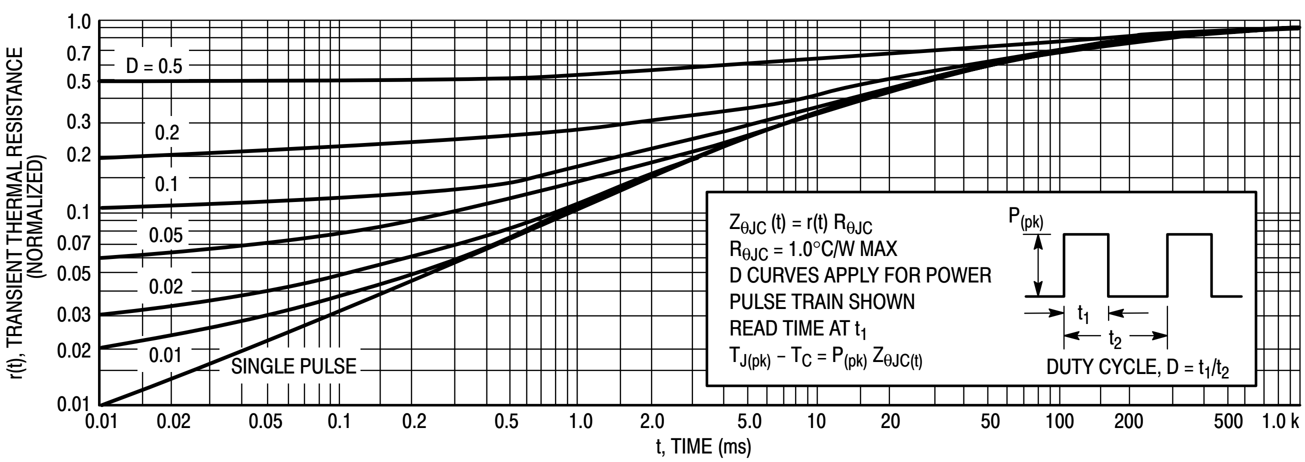
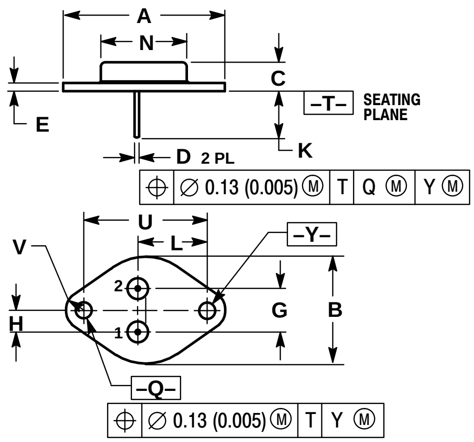


Figure 10. Thermal Response

PACKAGE DIMENSIONS

CASE 1–07
TO–204AA (TO–3)
ISSUE Z



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO–204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	1.550 REF		39.37 REF	
B	---	1.050	---	26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
E	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
H	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N	---	0.830	---	21.08
Q	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4.77

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

Notes

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